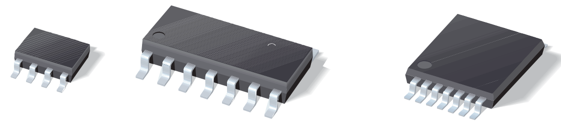


SLOS385 − SEPTEMBER 2001

LOW-NOISE, HIGH-SPEED CURRENT FEEDBACK AMPLIFIERS

FEATURES

- **Low Noise**
  - **2.9 pA/√Hz Noninverting Current Noise**
  - **10.8 pA/√Hz Inverting Current Noise**
  - **2.2 nV/√Hz Voltage Noise**
- **Wide Supply Voltage Range ±5 V to ±15 V**
- **Wide Output Swing**
  - **25 V_{PP} Output Voltage, R_L = 100 Ω, ±15-V Supply**
- **High Output Current, 150 mA (Min)**
- **High Speed**
  - **110 MHz (−3 dB, G=1, ±15 V)**
  - **1550 V/µs Slew Rate (G = 2, ±15 V)**
- **Low Distortion, G = 2**
  - **-78 dBc (1 MHz, 2 V_{PP}, 100-Ω load)**
- **Low Power Shutdown (THS3115)**
  - **300-µA Shutdown Quiescent Current Per Channel**
- **Thermal Shutdown and Short Circuit Protection**
- **Standard SOIC, SOIC PowerPAD™, and TSSOP PowerPAD™ Package**
- **Evaluation Module Available**

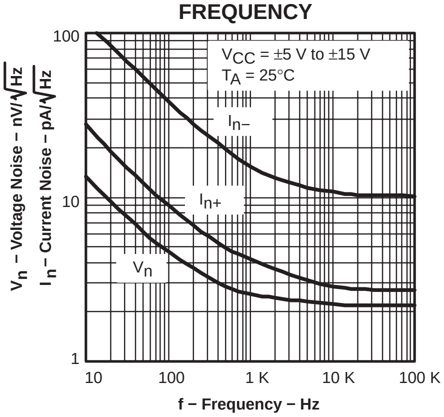
APPLICATIONS

- **Communication Equipment**
- **Video Distribution**
- **Motor Drivers**
- **Piezo Drivers**

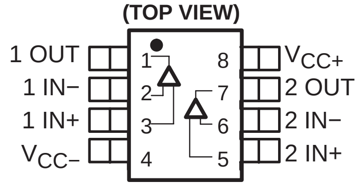
DESCRIPTION

The THS3112/5 are low-noise, high-speed current feedback amplifiers, ideal for any application requiring high output current. The low noninverting current noise of 2.9 pA/√Hz and the low inverting current noise of 10.8 pA/√Hz increase signal to noise ratios for enhanced signal resolution. The THS3112/5 can operate from ±5-V to ±15-V supply voltages, while drawing as little as 4.5 mA of supply current per channel. It offers low –78-dBc total harmonic distortion driving 2 V_{PP} into a 100-Ω load. The THS3115 features a low power shutdown mode, consuming only 300-µA shutdown quiescent current per channel. The THS3112/5 is packaged in a standard SOIC, SOIC PowerPAD™, and TSSOP PowerPAD packages.

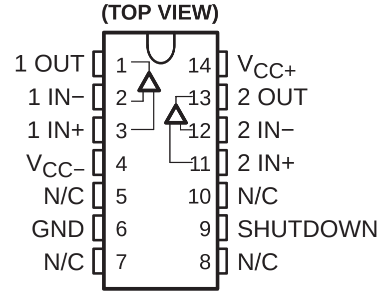
VOLTAGE NOISE AND CURRENT NOISE vs FREQUENCY



THS3112 SOIC (D) AND SOIC PowerPAD™ (DDA) PACKAGE (TOP VIEW)



THS3115 SOIC (D) AND TSSOP PowerPAD™ (PWP) PACKAGE (TOP VIEW)



AVAILABLE OPTIONS

T_A	PACKAGED DEVICE				EVALUATION MODULES
	SOIC-8 (D)	SOIC-8 PowerPAD (DDA)	SOIC-14 (D)	TSSOP-14 (PWP)	
0°C to 70°C	THS3112CD	THS3112CDDA	THS3115CD	THS3115CPWP	THS3112EVM THS3115EVM
−40°C to 85°C	THS3112ID	THS3112IDDA	THS3115ID	THS3115IPWP	

absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

- Supply voltage, V_{CC+} to V_{CC-} .... 33 V
- Input voltage .... ± V_{CC}
- Output current (see Note 1) .... 275 mA
- Differential input voltage .... ± 4 V
- Maximum junction temperature .... 150°C
- Total power dissipation at (or below) 25°C free-air temperature .... See Dissipation Ratings Table
- Operating free-air temperature, T_A: Commercial .... 0°C to 70°C
  - Industrial .... −40°C to 85°C
- Storage temperature, T_{stg} : Commercial .... −65°C to 125°C
  - Industrial .... −65°C to 125°C
- Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds .... 300°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: The THS3112 and THS3115 may incorporate a PowerPAD™ on the underside of the chip. This acts as a heatsink and must be connected to a thermally dissipating plane for proper power dissipation. Failure to do so may result in exceeding the maximum junction temperature which could permanently damage the device. See TI Technical Brief SLMA002 for more information about utilizing the PowerPAD™ thermally enhanced package.

DISSIPATION RATING TABLE

PACKAGE	θ_{JA}	T_A = 25°C POWER RATING
D-8	95°C/W‡	1.32 W
DDA	67°C/W	1.87 W
D-14	66.6°C/W‡	1.88 W
PWP	37.5°C/W	3.3 W

‡ This data was taken using the JEDEC proposed high-K test PCB. For the JEDEC low-K test PCB, the θ_{JA} is168°C/W for the D-8 package and 122.3°C/W for the D-14 package.

recommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, V_{CC+} to V_{CC-}	Dual supply	±5		±15	V
	Single supply	10		30	
Operating free-air temperature, T_A	C-suffix	0		70	°C
	I-suffix	−40		85	
Shutdown pin input levels, relative to the GND pin	High level (device shutdown)	2			V
	Low level (device active)			0.8	

electrical characteristics over recommended operating free-air temperature range, T_A = 25°C, V_{CC} = ±15 V, R_F = 750 Ω, R_L = 100 Ω (unless otherwise noted)

dynamic performance

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
BW	Small-signal bandwidth (−3 dB)	R_L = 100 Ω	R_F = 1 kΩ, G = 1	V_{CC} = ±5 V		95		MHz
				V_{CC} = ±15 V		110		
		R_L = 100 Ω	R_F = 750 Ω, G = 2	V_{CC} = ±5 V		103		
				V_{CC} = ±15 V		110		
	Bandwidth (0.1 dB)		R_F = 750 Ω, G = 2	V_{CC} = ±5 V		25		
				V_{CC} = ±15 V		48		
SR	Slew rate (see Note 2), G=8	G = 2, R_F = 680 Ω	V_O = 10 V_{PP}	V_{CC} = ±15 V		1550		V/µs
			V_O = 5 V_{PP}	V_{CC} = ±5 V		820		
				V_{CC} = ±15 V		1300		
t_s	Settling time to 0.1%	G = −1	V_O = 2 V_{PP}	V_{CC} = ±5 V		50		ns
			V_O = 5 V_{PP}	V_{CC} = ±15 V		63		

NOTE 2: Slew rate is defined from the 25% to the 75% output levels.

noise/distortion performance

PARAMETER			TEST CONDITIONS		MIN	TYP	MAX	UNIT
THD	Total harmonic distortion		G = 2, R_F = 680 Ω, V_{CC} = ±15 V, f = 1 MHz	$V_{O(PP)}$ = 2 V		−78		dBc
				$V_{O(PP)}$ = 8 V		−75		
			G = 2, R_F = 680 Ω, V_{CC} = ±5 V, f = 1 MHz	$V_{O(PP)}$ = 2 V		−76		
				$V_{O(PP)}$ = 6 V		−74		
V_n	Input voltage noise		V_{CC} = ±5 V, ±15 V	f = 10 kHz		2.2		nV/√Hz
I_n	Input current noise	Noninverting Input	V_{CC} = ±5 V, ±15 V	f = 10 kHz		2.9		pA/√Hz
		Inverting Input				10.8		
	Crosstalk		G = 2, f = 1 MHz, V_O = 2 Vpp	V_{CC} = ±5 V		−67		dBc
				V_{CC} = ±15 V		−67		
	Differential gain error		G = 2, R_L = 150 Ω, 40 IRE modulation, ±100 IRE Ramp, NTSC and PAL	V_{CC} = ±5 V		0.01%		
				V_{CC} = ±15 V		0.01%		
	Differential phase error			V_{CC} = ±5 V		0.011°		
				V_{CC} = ±15 V		0.011°		

electrical characteristics over recommended operating free-air temperature range, T_A = 25°C, V_{CC} = ±15 V, R_F = 750 Ω, R_L = 100 Ω (unless otherwise noted) (continued)

dc performance

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{IO}	Input offset voltage	V_{CC} = ±5 V, V_{CC} = ±15 V	T_A = 25°C		3	8	mV
			T_A = full range			13	
	Channel offset voltage matching		T_A = 25°C		1	3	
			T_A = full range			4	
	Offset drift		T_A = full range		10		μV/°C
I_{IB}	− Input bias current	V_{CC} = ±5 V, V_{CC} = ±15 V	T_A = 25°C			23	μA
			T_A = full range			30	
	+ Input bias current		T_A = 25°C		0.33	2	
			T_A = full range			3	
	Input offset current		T_A = 25°C		4	22	
			T_A = full range			30	
Z_{OL}	Open loop transimpedance	V_{CC} = ±5 V, V_{CC} = ±15 V	R_L = 1 kΩ,		1		MΩ

input characteristics

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{ICR}	Input common-mode voltage range	V_{CC} = ±5 V	T_A = full range	±2.5	±2.7		V
		V_{CC} = ±15 V		±12.5	±12.7		
CMRR	Common-mode rejection ratio	V_{CC} = ±5 V, V_I = −2.5 V to 2.5 V	T_A = 25°C	56	62		dB
			T_A = full range	54			
		V_{CC} = ±15 V, V_I = −12.5 V to 12.5 V	T_A = 25°C	63	67		
			T_A = full range	60			
R_I	Input resistance	+ Input			1.5		MΩ
		− Input			15		Ω
C_i	Input capacitance				2		pF

output characteristics

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
V_O	Output voltage swing	G = 4, V_I = 1 V, V_{CC} = ±5 V	R_L = 1 kΩ,	T_A = 25°C		3.9		V
			R_L = 100 Ω,	T_A = 25°C	3.6	3.8		
				T_A = full range	3.4			
		G = 4, V_I = 3.4 V, V_{CC} = ±15 V	R_L = 1 kΩ,	T_A = 25°C		13.5		
			R_L = 100 Ω,	T_A = 25°C	12.2	13.3		
				T_A = full range	12			
I_O	Output current drive	G = 4, V_I = 0.9 V, V_{CC} = ±5 V	R_L = 25 Ω,	T_A = 25°C	100	130		mA
		G = 4, V_I = 1.7 V, V_{CC} = ±15 V	R_L = 25 Ω,		175	270		
r_o	Output resistance	open loop				14		Ω

electrical characteristics over recommended operating free-air temperature range, T_A = 25°C, V_{CC} = ±15 V, R_F = 750 Ω, R_L = 100 Ω, GND = 0 V (unless otherwise noted) (continued)

power supply

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
I_{CC}	Quiescent current (per amplifier)	V_{CC} = ±5 V	T_A = 25°C		4.4	5.5	mA
			T_A = full range			6	
		V_{CC} = ±15 V	T_A = 25°C		4.9	6.5	
			T_A = full range			7.5	
PSRR	Power supply rejection ratio	V_{CC} = ±5 V	T_A = 25°C	53	60		dB
			T_A = full range	50			
		V_{CC} = ±15 V	T_A = 25°C	68	74		
			T_A = full range	66			

shutdown characteristics (THS3115 only)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$I_{CC(SHDN)}$	Shutdown quiescent current (per channel)	V_{GND} = 0 V, V_{CC} = ±5 V, ±15 V		0.3	0.45	mA
t_{DIS}	Disable time (see Note 3)	V_{CC} = ±15 V		200		ns
t_{EN}	Enable time (see Note 3)	V_{CC} = ±15 V		300		ns
$I_{IL(SHDN)}$	Shutdown pin input bias current for power up	V_{CC} = ±5 V, ±15 V, $V_{(SHDN)}$ = 0 V		18	25	µA
$I_{IH(SHDN)}$	Shutdown pin input bias current for power down	V_{CC} = ±5 V, ±15 V, $V_{(SHDN)}$ = 3.3 V		110	130	µA

NOTE 3: Disable/enable time is defined as the time from when the shutdown signal is applied to the SHDN pin to when the supply current has reached half of its final value.

TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
	Small signal closed loop gain	vs Frequency	1 − 11, 13, 14
	Gain and phase	vs Frequency	12
	Small signal closed loop noninverting gain	vs Frequency	15, 16
	Small signal closed loop inverting gain	vs Frequency	17, 18
	Small and large signal output	vs Frequency	19, 20
	Harmonic distortion	vs Frequency	21, 22
		vs Peak−to−peak output voltage	23, 24
V_n, I_n	Voltage noise and current noise	vs Frequency	25
CMRR	Common-mode rejection ratio	vs Frequency	26
PSRR	Power supply rejection ratio	vs Frequency	27
	Crosstalk	vs Frequency	28
Z_o	Output impedance	vs Frequency	29
SR	Slew rate	vs Output voltage step	30
V_{IO}	Input offset voltage	vs Free-air temperature	31
		vs Common-mode input voltage	32
I_B	Input bias current	vs Free-air temperature	33
V_O	Output voltage	vs Output current	34, 35
	Output voltage headroom	vs Output current	36
I_{CC}	Supply current (per channel)	vs Supply voltage	37
	Shutdown response		38

TYPICAL CHARACTERISTICS

SMALL SIGNAL CLOSED LOOP GAIN vs FREQUENCY

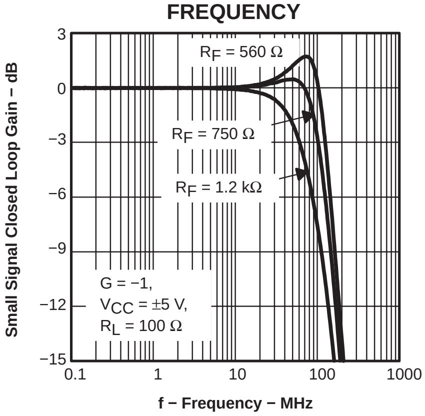


Figure 1

SMALL SIGNAL CLOSED LOOP GAIN vs FREQUENCY

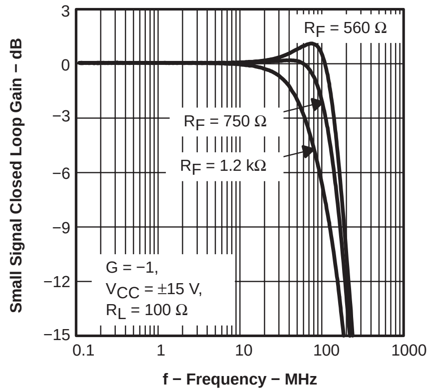


Figure 2

SMALL SIGNAL CLOSED LOOP GAIN vs FREQUENCY

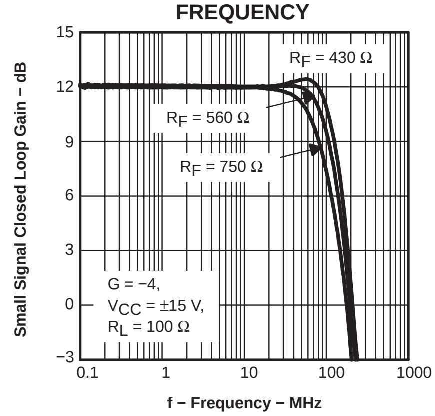


Figure 3

SMALL SIGNAL CLOSED LOOP GAIN vs FREQUENCY

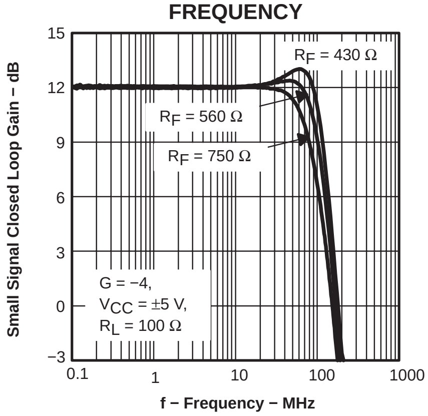


Figure 4

SMALL SIGNAL CLOSED LOOP GAIN vs FREQUENCY

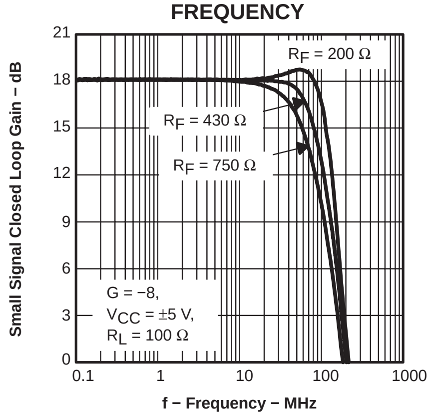


Figure 5

SMALL SIGNAL CLOSED LOOP GAIN vs FREQUENCY

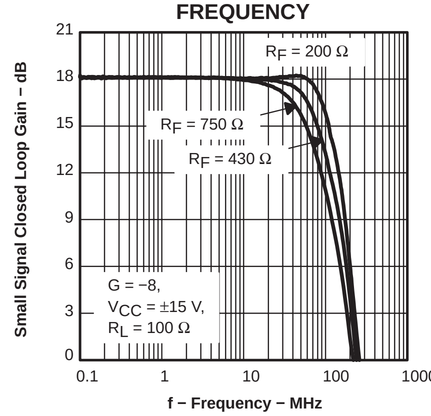


Figure 6

SMALL SIGNAL CLOSED LOOP GAIN vs FREQUENCY

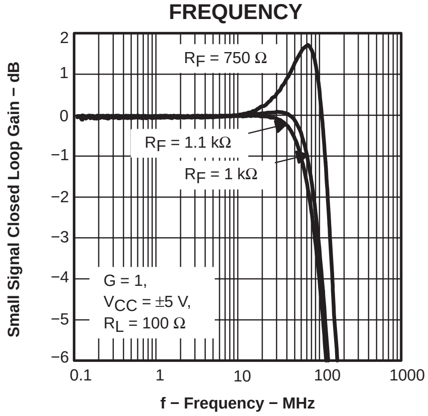


Figure 7

SMALL SIGNAL CLOSED LOOP GAIN vs FREQUENCY

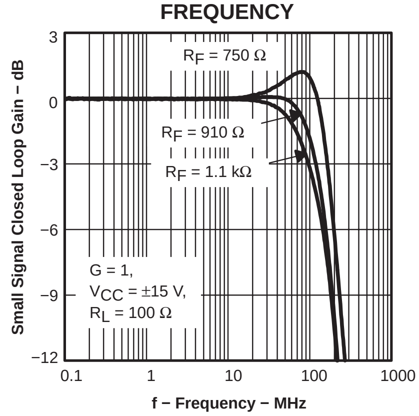


Figure 8

SMALL SIGNAL CLOSED LOOP GAIN vs FREQUENCY

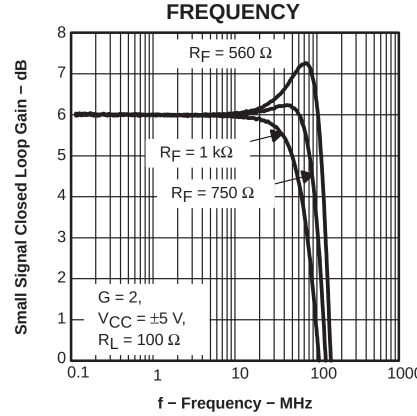


Figure 9

TYPICAL CHARACTERISTICS

SMALL SIGNAL CLOSED LOOP GAIN vs FREQUENCY

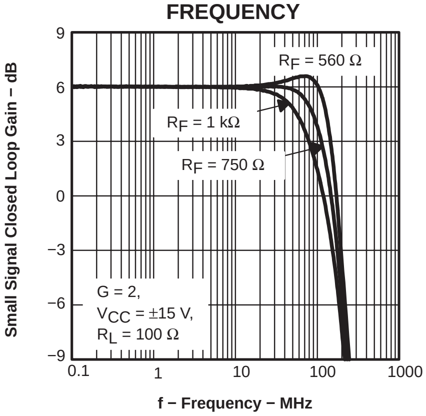


Figure 10

SMALL SIGNAL CLOSED LOOP GAIN vs FREQUENCY

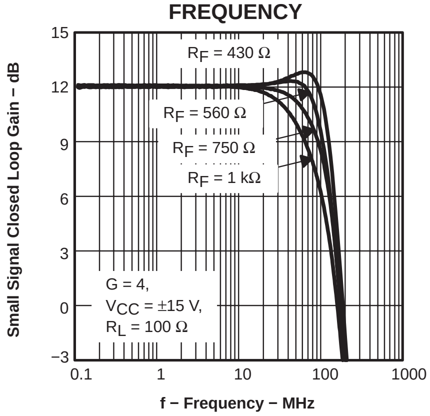


Figure 11

GAIN AND PHASE vs FREQUENCY

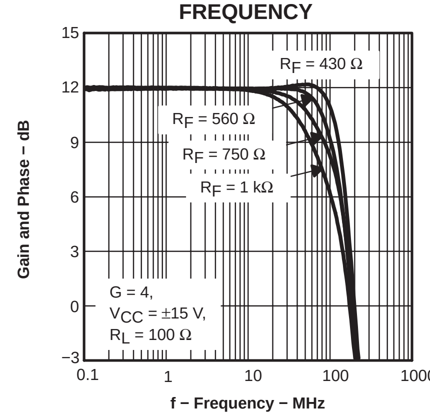


Figure 12

SMALL SIGNAL CLOSED LOOP GAIN vs FREQUENCY

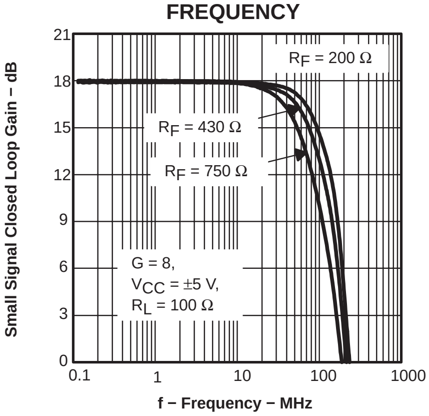


Figure 13

SMALL SIGNAL CLOSED LOOP GAIN vs FREQUENCY

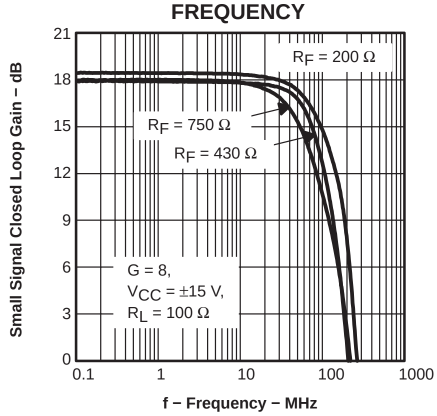


Figure 14

SMALL SIGNAL CLOSED LOOP NONINVERTING GAIN vs FREQUENCY

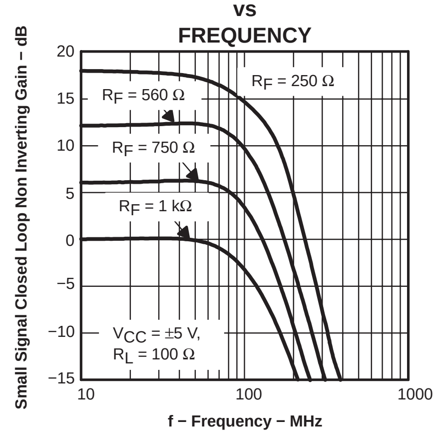


Figure 15

SMALL SIGNAL CLOSED LOOP NONINVERTING GAIN vs FREQUENCY

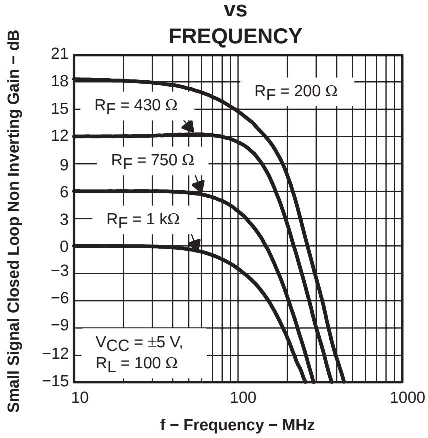


Figure 16

SMALL SIGNAL CLOSED LOOP INVERTING GAIN vs FREQUENCY

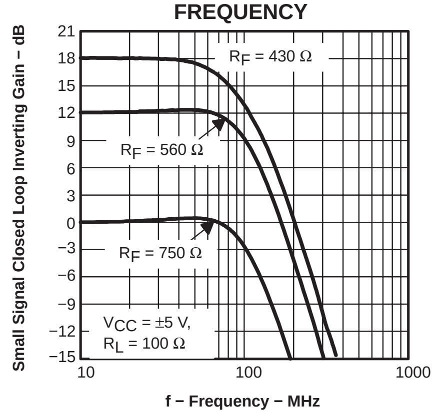


Figure 17

SMALL SIGNAL CLOSED LOOP INVERTING GAIN vs FREQUENCY

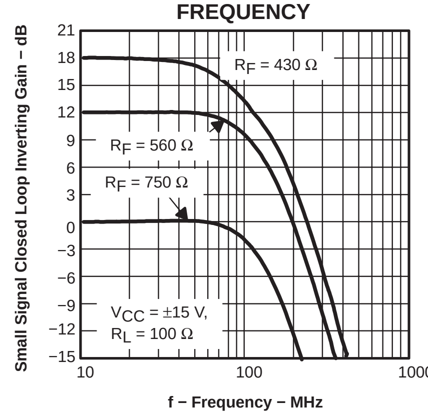


Figure 18

TYPICAL CHARACTERISTICS

SMALL AND LARGE SIGNAL OUTPUT vs FREQUENCY

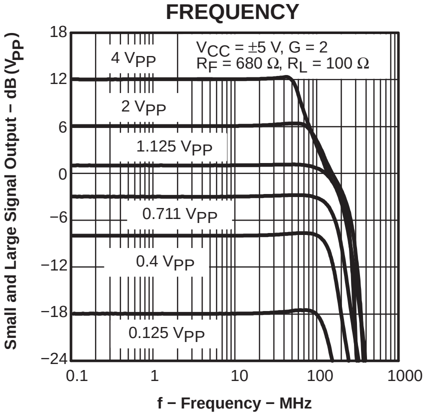


Figure 19

SMALL AND LARGE SIGNAL OUTPUT vs FREQUENCY

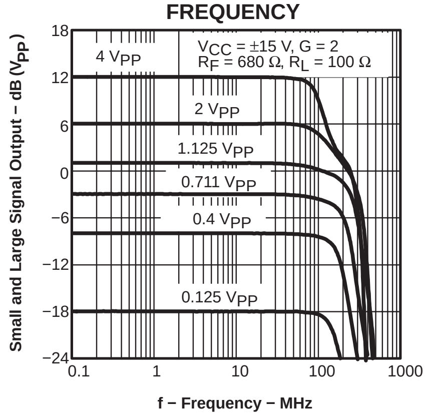


Figure 20

HARMONIC DISTORTION vs FREQUENCY

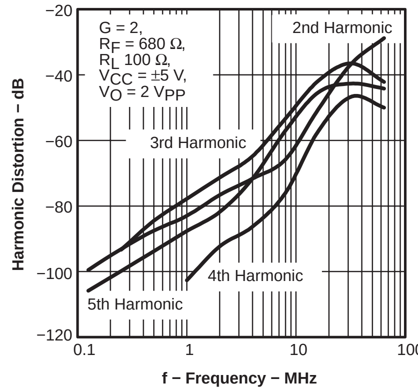


Figure 21

HARMONIC DISTORTION vs FREQUENCY

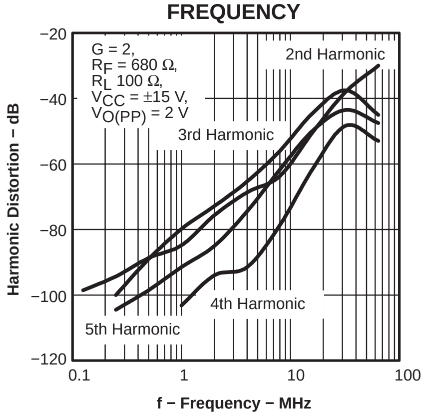


Figure 22

HARMONIC DISTORTION vs PEAK-TO-PEAK OUTPUT VOLTAGE

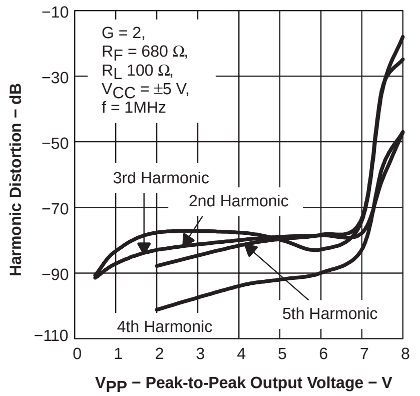


Figure 23

HARMONIC DISTORTION vs PEAK-TO-PEAK OUTPUT VOLTAGE

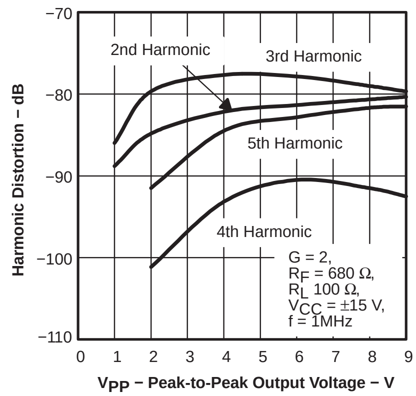


Figure 24

VOLTAGE NOISE AND CURRENT NOISE vs FREQUENCY

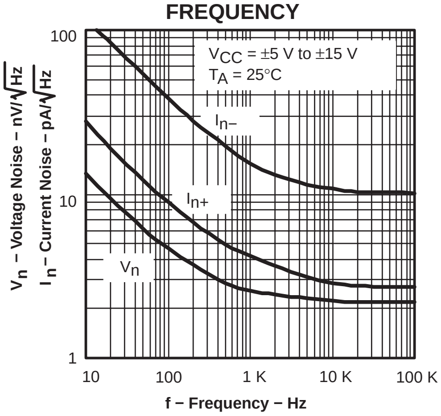


Figure 25

COMMON-MODE REJECTION RATIO vs FREQUENCY

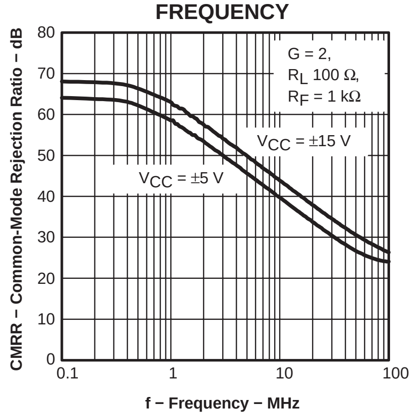


Figure 26

POWER SUPPLY REJECTION RATIO vs FREQUENCY

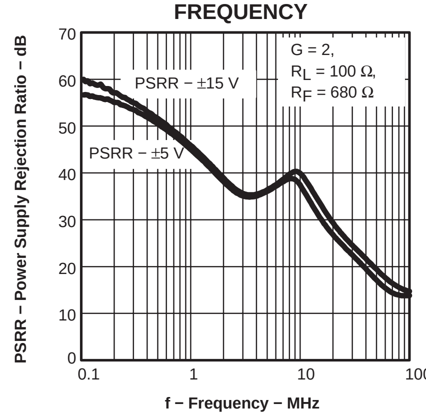


Figure 27

TYPICAL CHARACTERISTICS

CROSSTALK vs FREQUENCY

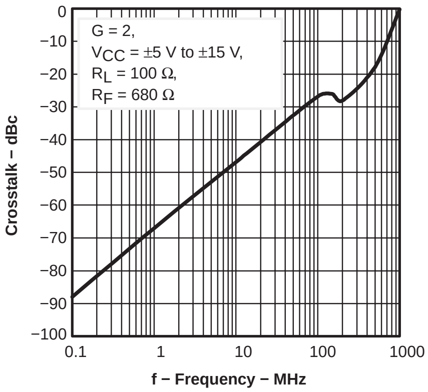


Figure 28

OUTPUT IMPEDANCE vs FREQUENCY

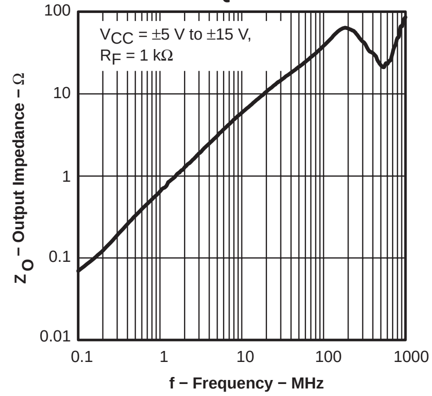


Figure 29

SLEW RATE vs OUTPUT VOLTAGE STEP

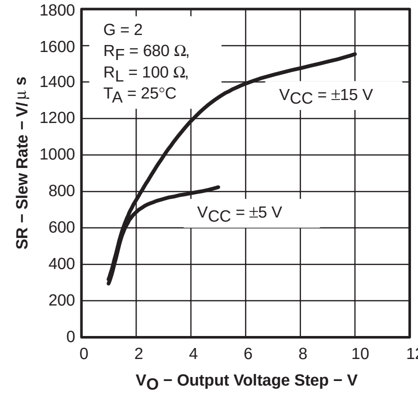


Figure 30

INPUT OFFSET VOLTAGE vs FREE-AIR TEMPERATURE

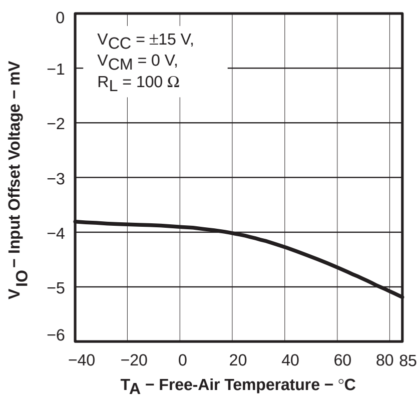


Figure 31

INPUT OFFSET VOLTAGE vs COMMON-MODE INPUT VOLTAGE

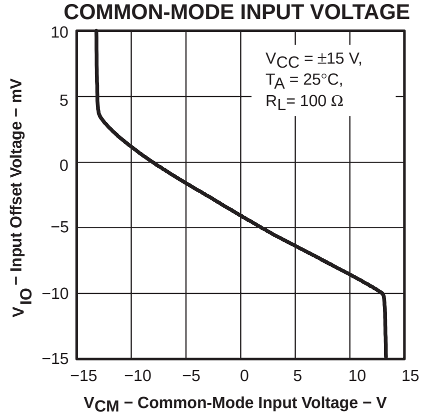


Figure 32

INPUT BIAS CURRENT vs FREE-AIR TEMPERATURE

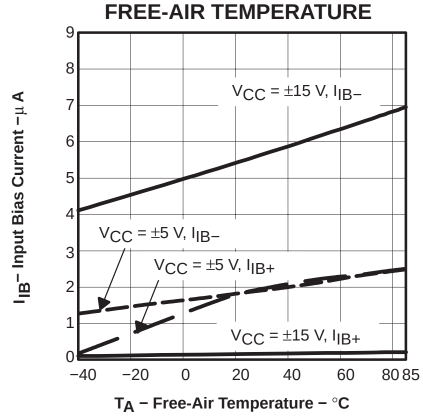


Figure 33

OUTPUT VOLTAGE vs OUTPUT CURRENT

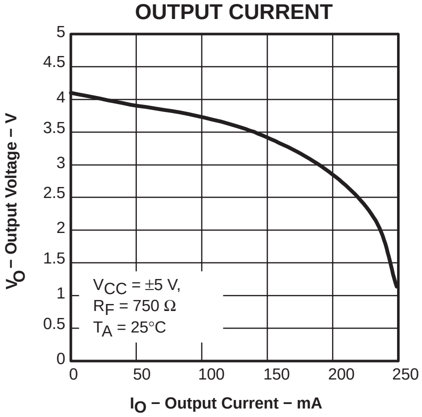


Figure 34

OUTPUT VOLTAGE vs OUTPUT CURRENT

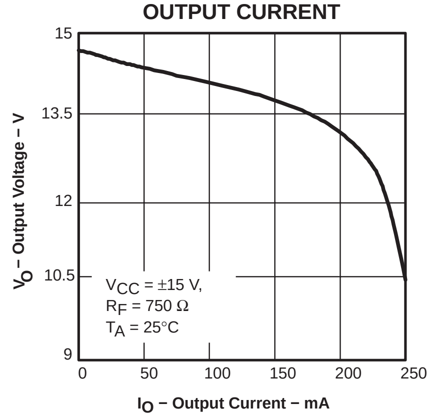


Figure 35

OUTPUT VOLTAGE HEADROOM vs OUTPUT CURRENT

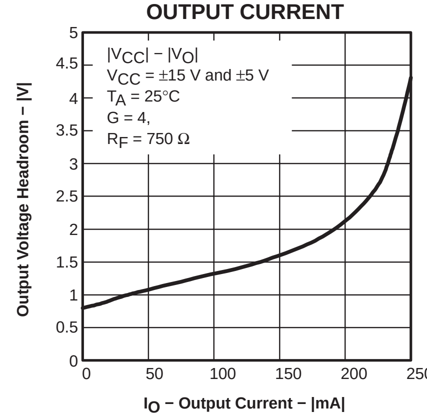


Figure 36

TYPICAL CHARACTERISTICS

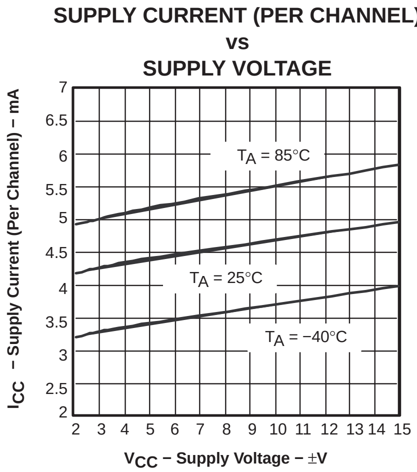


Figure 37

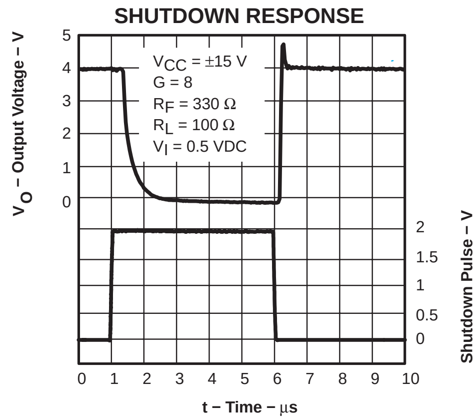


Figure 38

PACKAGING INFORMATION

Orderable Device	Status [1]	Package Type	Package Drawing	Pins	Package Qty	Eco Plan [2]	Lead/Ball Finish	MSL Peak Temp [3]
THS3112CD	ACTIVE	SOIC	D	8	75	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
THS3112CDDA	ACTIVE	SO Power PAD	DDA	8	75	None	CU SNPB	Level-1-235C-UNLIM
THS3112CDDAR	ACTIVE	SO Power PAD	DDA	8	2500	None	CU SNPB	Level-1-235C-UNLIM
THS3112CDR	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
THS3112ID	ACTIVE	SOIC	D	8	75	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
THS3112IDDA	ACTIVE	SO Power PAD	DDA	8	75	None	CU SNPB	Level-1-235C-UNLIM
THS3112IDDAR	ACTIVE	SO Power PAD	DDA	8	2500	None	CU SNPB	Level-1-235C-UNLIM
THS3112IDR	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
THS3115CD	ACTIVE	SOIC	D	14	50	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
THS3115CDR	ACTIVE	SOIC	D	14	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
THS3115CPWP	ACTIVE	HTSSOP	PWP	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
THS3115CPWPR	ACTIVE	HTSSOP	PWP	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
THS3115ID	ACTIVE	SOIC	D	14	75	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
THS3115IDR	ACTIVE	SOIC	D	14	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
THS3115IPWP	ACTIVE	HTSSOP	PWP	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
THS3115IPWPR	ACTIVE	HTSSOP	PWP	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

[1] The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

[2] Eco Plan - May not be currently available - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
None: Not yet available Lead (Pb-Free).
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Green (RoHS & no Sb/Br): TI defines "Green" to mean "Pb-Free" and in addition, uses package materials that do not contain halogens, including bromine (Br) or antimony (Sb) above 0.1% of total product weight.

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDECindustry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

Mailing Address: Texas Instruments
Post Office Box 655303 Dallas, Texas 75265